Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	2	"20030047750".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/24 10:14
L3	6	"238699".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/24 10:46
L4	4355	((257/173) or (257/174) or (257/355) or (257/356) or (257/257) or (257/357) or (257/358) or (257/359) or (257/360) or (257/361) or (257/362) or (257/363)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/24 10:47
L5	92	4 and (radio adj frequency RF) and (esd electrostatic adj discharge) and (cmos bicmos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/24 10:49
S1	3	"823244".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 23:36
S2	491	(257/173).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 18:31
S3	32	S2 and semiconductor near2 diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 15:29
S4	52	S2 and zener near2 diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 15:30
S5	39	(S2 and zener near2 diode) not S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 15:30

S6	0	("deepadjwellnear10shallowadjwel landesd").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 18:31
S7	0	deep adj well near10 shallow adj well and esd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 18:32
S8	18	double adj well and esd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 18:37
S9	1625	((257/355) or (257/356) or (257/357) or (257/358)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/09/25 00:30
S10	243	S9 and (second deep shallow) adj2 well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 20:29
S11	78	S9 and (second deep shallow) adj2 well and "well" near5 "within" near5 "well"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 19:12
S12	0	zener adj diode near4 backside near4 substrate and esd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 19:13
S13	0	zener adj diode near4 back-side near4 substrate and esd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 19:13
S14	0	zener adj diode near6 back-side near6 substrate and esd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 19:13
S15	0	zener adj diode near6 back-side near6 substrate and (protecting protection esd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 19:14

EAST Search History

S16	3	diode near6 back-side near6 substrate and (protecting protection esd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 19:14
S17	1875	((257/355) or (257/356) or (257/357) or (257/358) or (257/173) or (257/174)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/05/29 20:28
S18	269	S17 and (second deep shallow) adj2 well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 20:29
S19	188	S17 and (second deep shallow) adj2 well and esd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 20:29
S20	2	("5932898").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 23:45
S21	2	("6891207").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 23:45
S22	1944	((257/355) or (257/356) or (257/357) or (257/358) or (257/173) or (257/174)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/09/25 00:31
S23	404	S22 and (doping dopant impurity impurities) near6 ("small" "smaller" "lower" "less" "larger" "greater")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/25 00:34
S24	335	S22 and (doping dopant impurity impurities) near6 ("small" "smaller" "lower" "less" "larger" "greater")	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/09/25 01:09
S25	2	("20030047750").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/25 04:21

EAST Search History

S26	0	("234244.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/08 13:23
S27	0	("823244.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/08 13:23
S28	4	"823244".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/08 13:24
S29	1	(US-20050224917-$).did.	US-PGPUB	OR	OFF	2005/12/08 13:27
S30	1	S29 and embedded and concentration and (equal identical "same" similar)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 13:28
S31	2	("20030047750").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/05 19:28
S32	0	additional adj substrate near6 (npn pnp) with (esd protect$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/05 19:29
S33	0	second adj substrate near6 (npn pnp) with (esd protect$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/05 19:29
S34	200	substrate near6 (npn pnp) with (esd protect$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/05 19:30
S35	200	substrate near6 (npn pnp) with (esd protect$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/05 19:30

S36	41	substrate near6 (npn pnp) with (esd protect$3) and cathode and anode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/05 19:35
S37	711	(npn pnp) with (esd protect$3) and cathode and anode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/05 19:36
S38	25	substrate near6 (npn pnp) near6 (esd protect$3) and cathode and anode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/05 19:42
S39	2038	((257/173) or (257/355)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/05 19:43
S40	180	S39 and substrate near6 (npn pnp)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/05 19:43
S41	180	S39 and substrate near6 (npn pnp)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/05 19:46
S42	17	triple adj "well" and S40	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/05 19:46
S43	5	triple adj "well" near6 esd and S40	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/05 19:49
S44	6	triple adj "well" near6 esd and S39	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/05 19:51
S45	6	triple adj "well" near6 (electrostatic adj discharge esd) and S39	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/05 19:52

EAST Search History

S46	14	triple adj "well" near6 (electrostatic adj discharge esd).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/05 20:16
S47	2	"20040232450"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/05 20:17
S48	2888	((257/173) or (257/174) or (257/355) or (257/356) or (257/357) or (257/358)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 08:06
S49	0	S48 and junction adj diode.ti,ab, clm. and triple adj "well" and (concentration density).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 08:08
S50	1	S48 and junction adj diode.ti,ab, clm. and third adj "well" and (concentration density).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 08:19
S51	0	amerasekara.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 08:19